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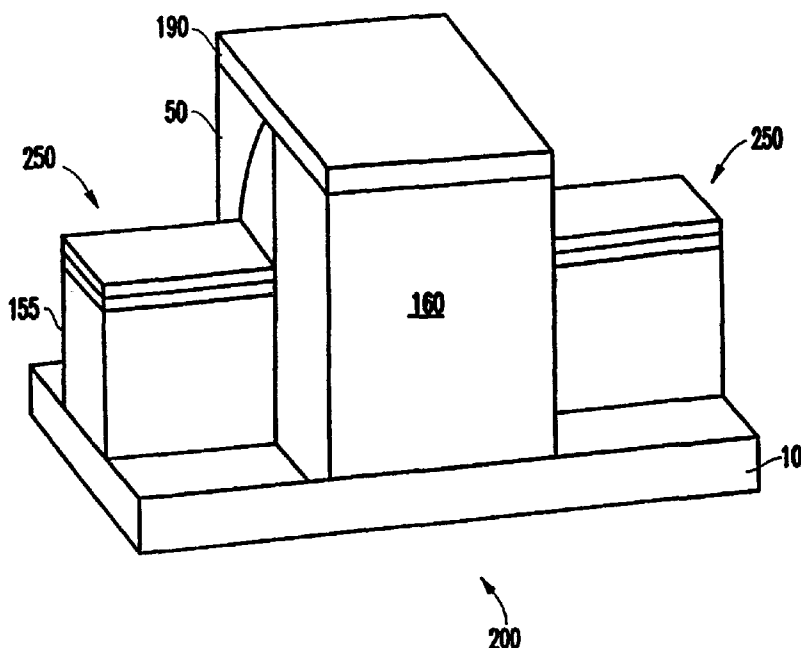
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(54) Title: STRAINED FIN FETS STRUCTURE AND METHOD



(57) Abstract: A structure for a transistor that includes an insulator (10) and a silicon structure on the insulator. The silicon structure includes a central portion (155) and Fins (250) extending from ends of the central portion. A first gate (50) is positioned on a first side of the central portion of the silicon structure. A strain-producing layer (11) could be between the first gate (50) and the first side of the central portion (155) of the silicon structure and a second gate (160) is on a second side of the central portion (155) of the silicon structure.



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